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November 2013

FQP13N50C / FQPF13N50C

N-Channel QFET® MOSFET

500 V, 13 A, 480 mΩ

Description

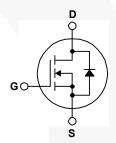
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize onstate resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.

Features

- 13 A, 500 V, $R_{\rm DS(on)}$ = 480 m Ω (Max.) @ $V_{\rm GS}$ = 10 V, $I_{\rm D}$ = 6.5 A
- Low Gate Charge (Typ. 43 nC)
- Low Crss (Typ. 20 pF)
- 100% Avalanche Tested







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP13N50C	FQPF13N50C	Units
V_{DSS}	Drain-Source Voltage		5	00	V
I _D	Drain Current - Continuous (T _C = 25°C)		13	13 *	Α
	- Continuous (T _C =	100°C)	8	8 *	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	52	52 *	Α
V _{GSS}	Gate-Source Voltage		± 30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		860		mJ
I _{AR}	Avalanche Current	(Note 1)	13		Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		19.5		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5		V/ns
P_D	Power Dissipation (T _C = 25°C)		195	48	W
	- Derate above 25°C		1.56	0.39	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to	+150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300		°C
.r					O

^{*} Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQP13N50C	FQPF13N50C	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.64	2.58	°C/W
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP13N50C_F105	FQP13N50C	TO-220	Tube	N/A	N/A	50 units
FQPF13N50C_F105	FQPF13N50C	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	500			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		0.5		V/°C
I _{DSS} Zero Gate Voltage Drain Current	Zara Octa Vallana Basia Occasat	V _{DS} = 500 V, V _{GS} = 0 V			1	μΑ
	V _{DS} = 400 V, T _C = 125°C			10	μΑ	
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V		-	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 6.5 A		0.39	0.48	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 6.5 A		15		S
Dynami	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1580	2055	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		180	235	pF
C _{rss}	Reverse Transfer Capacitance			20	25	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250 V, I _D = 13 A,		25	60	ns
t _r	Turn-On Rise Time	$R_{G} = 25 \Omega$		100	210	ns
t _{d(off)}	Turn-Off Delay Time			130	270	ns
t _f	Turn-Off Fall Time	(Note 4)		100	210	ns
Qg	Total Gate Charge	V _{DS} = 400 V, I _D = 13 A,		43	56	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	/	7.5		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		18.5		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				13	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current			-	52	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 13 A		-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 13 A,		410	//	ns
Q _{rr}	Reverse Recovery Charge	dl _F / dt = 100 A/μs		4.5		μС

Notes:

- Notes. 1. Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 6 mH, I_{AS} = 13 A, V_{DD} = 50 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3. $I_{SD} \le 13$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, starting T_{J} = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

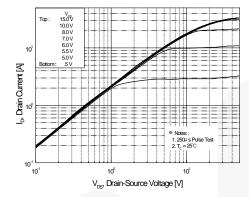


Figure 1. On-Region Characteristics

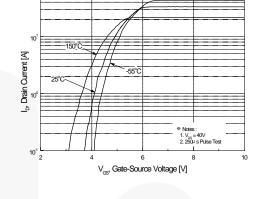


Figure 2. Transfer Characteristics

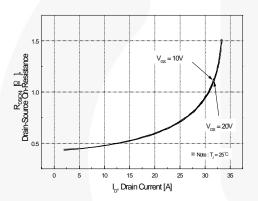


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

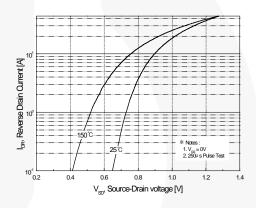


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

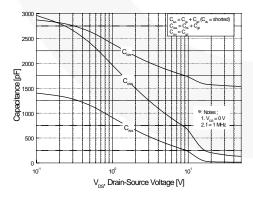


Figure 5. Capacitance Characteristics

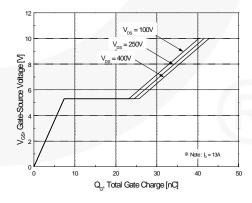


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

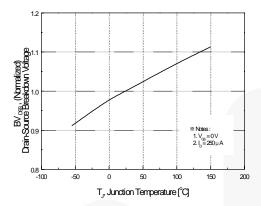


Figure 7. Breakdown Voltage Variation vs Temperature

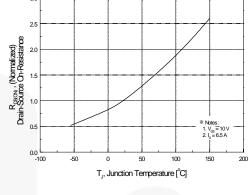


Figure 8. On-Resistance Variation vs Temperature

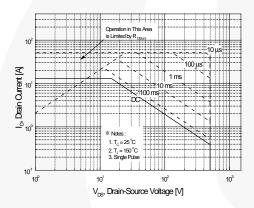


Figure 9-1. Maximum Safe Operating Area for FQP13N50C

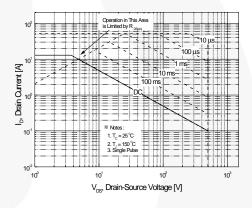


Figure 9-2. Maximum Safe Operating Area for FQPF13N50C

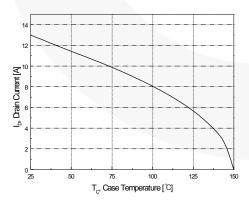


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (continued)

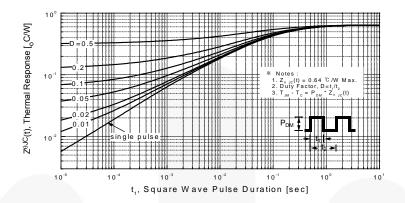


Figure 11-1. Transient Thermal Response Curve for FQP13N50C

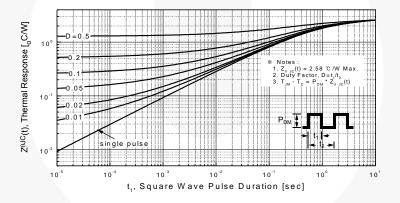


Figure 11-2. Transient Thermal Response Curve for FQPF13N50C

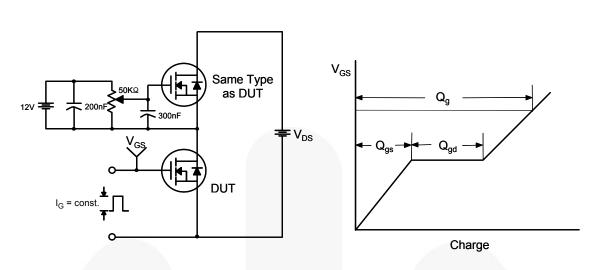


Figure 12. Gate Charge Test Circuit & Waveform

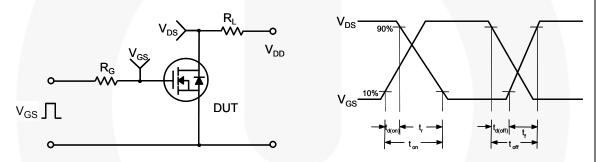


Figure 13. Resistive Switching Test Circuit & Waveforms

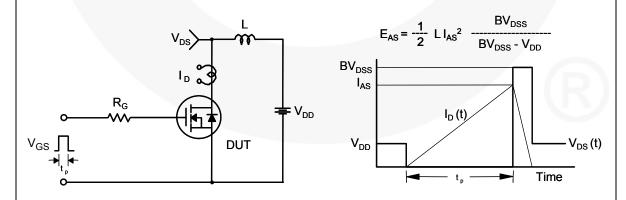
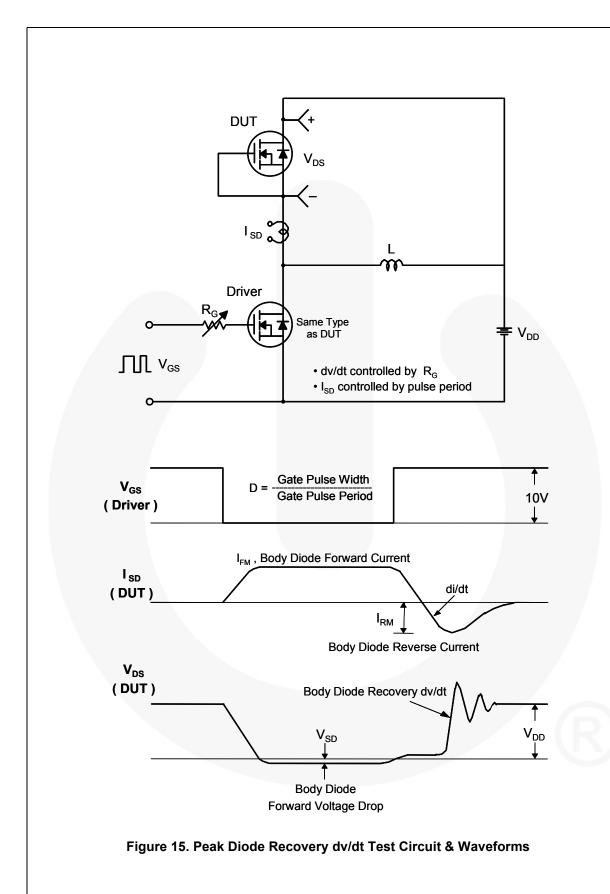


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

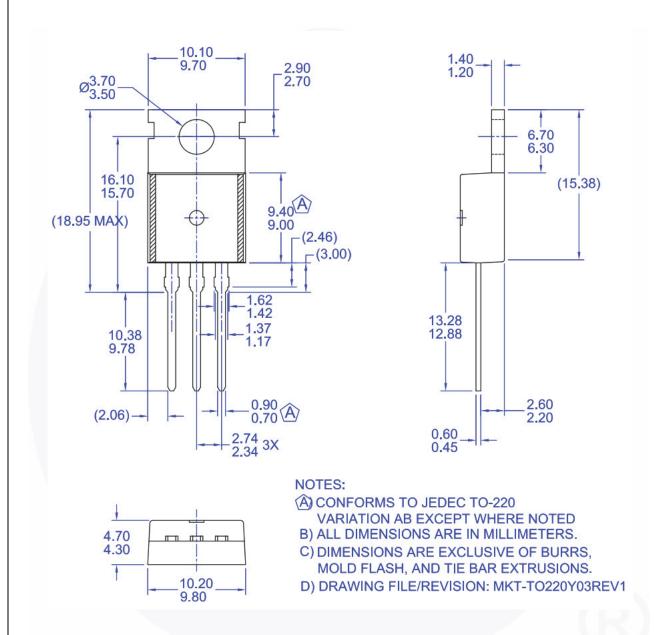


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

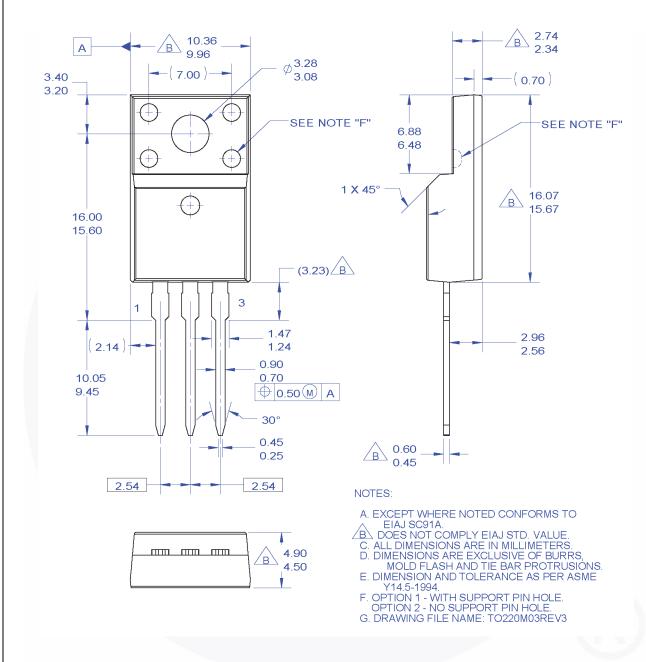


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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